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FCA35N60 N-Channel SuperFET[®] MOSFET 600 V, 35 A, 98 m Ω

May 2014

Features

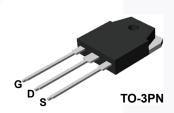
- 650V @ T_{.I} = 150°C
- Typ. $R_{DS(on)}$ = 79 m Ω
- Ultra Low Gate Charge (Typ. $Q_g = 139 \text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 340 pF$)
- · 100% Avalanche Tested

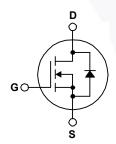
Applications

- · Solar Inverter
- AC-DC Power Supply

Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FCA35N60	Unit	
V _{DSS}	Drain to Source Voltage			600	V	
V _{GSS}	Gate-Soure voltage			±30	V	
	Drain Current	- Continuous (T _C = 25°C)		35	А	
ID	DrainCurrent	- Continuous (T _C = 100°C)		22.2	A	
I _{DM}	Drain Current	- Pulsed	- Pulsed (Note 1)		Α	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			1455	mJ	
I _{AR}	Avalanche Current (Note 1		(Note 1)	35	Α	
E _{AR}	Repetitive Avalanche Energy (Note 1		(Note 1)	31.25	mJ	
dv/dt	Peak Diode Recovery dv/d	It	(Note 3)	20	V/ns	
D	Dawer Dissipation	$(T_C = 25^{\circ}C)$		312.5	W	
P_{D}	Power Dissipation	- Derate Above 25°C		2.5	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
T _L	Maximum Lead Temperati	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			°C	

Thermal Characteristics

Symbol	Parameter	FCA35N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	42	*C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCA35N60	FCA35N60	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
D\/	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	600	-	-	V
BV_{DSS}	Drain to Source Breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 150^{\circ} C$	-	650	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.6	-	V/°C
BV _{DS}	Drain-Source Avalanche Breakdown Voltage	V _{GS} = 0 V, I _D = 16 A	-	700	-	V
	Zero Gate Voltage Drain Current	V _{DS} = 600 V, V _{GS} = 0 V	-	-	1	
I _{DSS}	Zeio Gale vollage Dialii Cuiteili	$V_{DS} = 480 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 17.5 A	-	0.079	0.098	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 17.5 \text{ A}$	1	28.8	1	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05.V.V 0.V	-	4990	6640	pF
C _{oss}	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		2380	3170	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 101112	-	140	-	pF
C _{oss}	Output Capacitance	V _{DS} = 480 V, V _{GS} = 0 V, f = 1 MHz	-	113	-	pF
Coss(eff.)	Effective Output Capacitance	V _{DS} = 0 V to 480 V, V _{GS} = 0 V		340	-	pF
Q_g	Total Gate Charge at 10V	V _{DS} = 480 V, I _D = 35 A,	-	139	181	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	31	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	69	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1.4	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		/-	34	78	ns
t _r		$V_{DD} = 300 \text{ V}, I_D = 35 \text{ A},$	/ -	120	250	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_G = 4.7 \Omega$	-	105	220	ns
t _f	Turn-Off Fall Time	(Note 4)	-	73	155	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Dioc	Maximum Continuous Drain to Source Diode Forward Current			35	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	105	Α
V_{SD}	Drain to Source Diode Forward Voltage V _{GS} = 0 V, I _{SD} = 35 A		-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 35 A,	-	614		ns
Q _{rr}	Reverse Recovery Charge $dI_F/dt = 100 A/\mu s$		-	16.3		μС

Notes:

- 1: Repetitive rating: pulse-width limited by maximum junction temperature.
- 2: I_{AS} = 17.5 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
- 3: I $_{SD}~\leq$ 35 A, di/dt \leq 200 A/ μ s, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

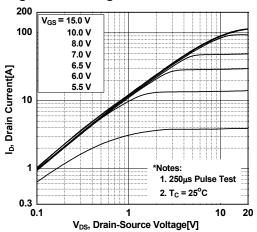


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

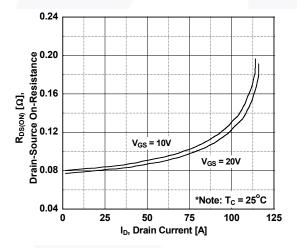


Figure 5. Capacitance Characteristics

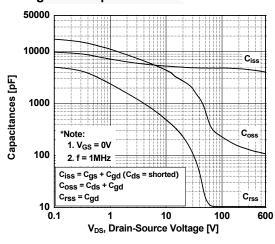


Figure 2. Transfer Characteristics

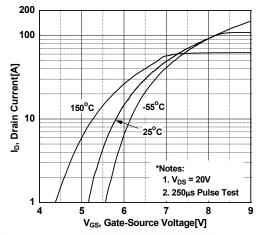


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

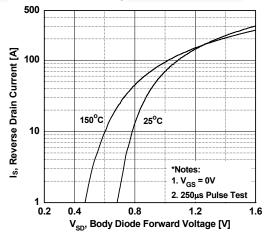
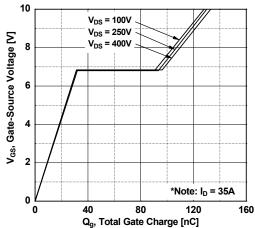


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

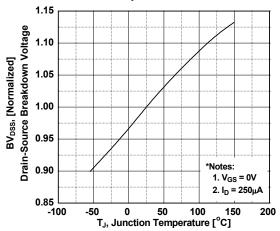


Figure 8. On-Resistance Variation vs. Temperature

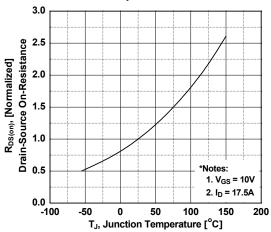


Figure 9. Maximum Safe Operating Area

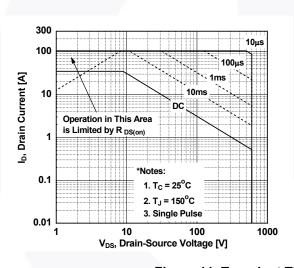


Figure 10. Maximum Drain Current vs. Case Temperature

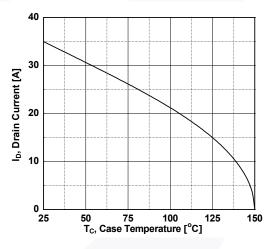
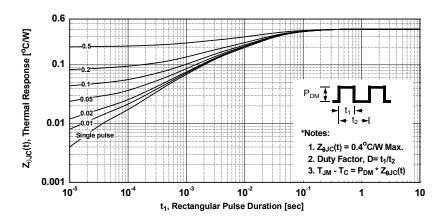


Figure 11. Transient Thermal Response Curve



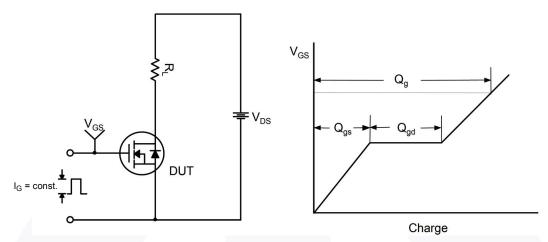


Figure 12. Gate Charge Test Circuit & Waveform

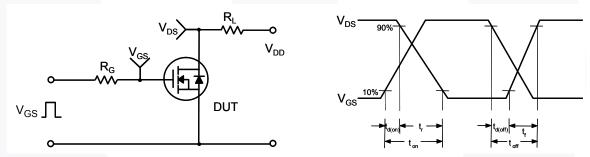


Figure 13. Resistive Switching Test Circuit & Waveforms

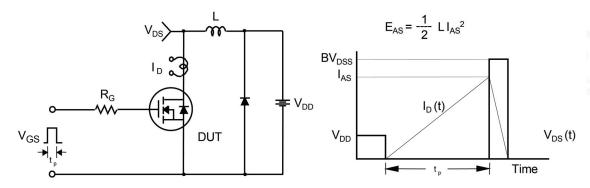


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

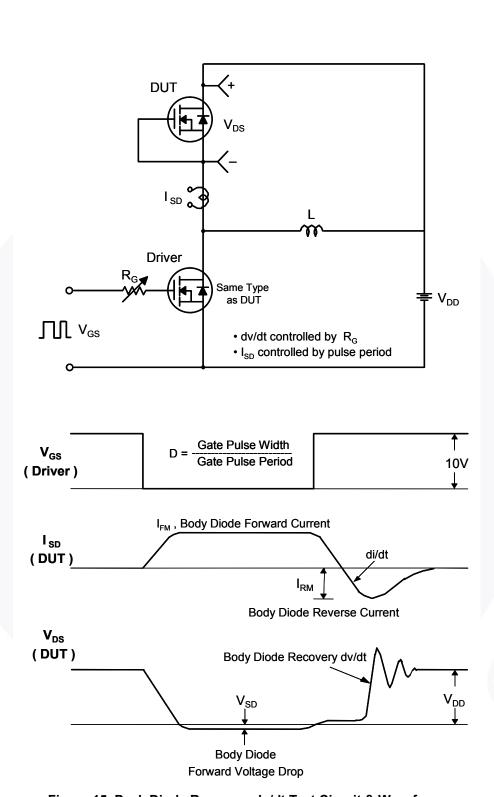
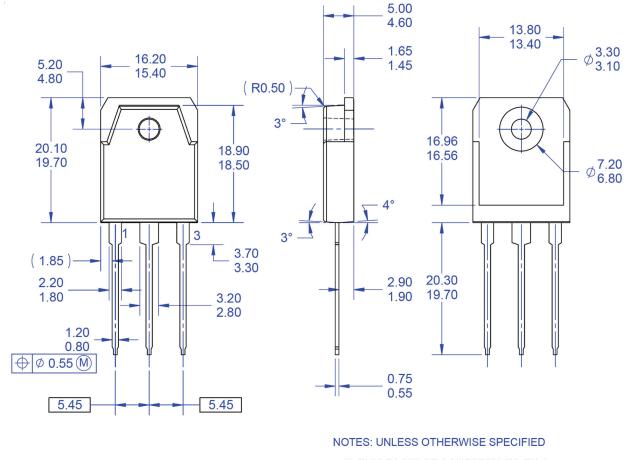
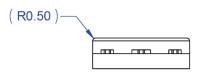


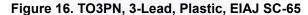
Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





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